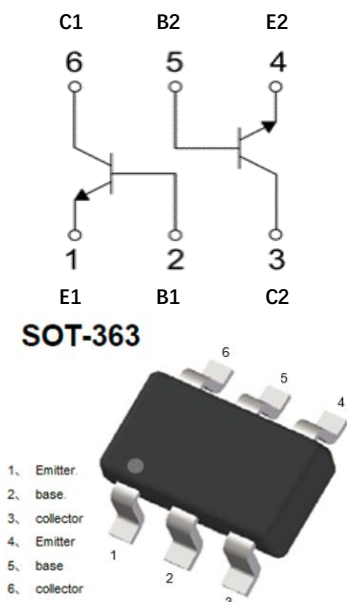


Dual NPN Small Signal Transistor



Features

- Moisture sensitivity level 1
- Halogen free and RoHS compliant
- Surface mount package ideally suited for automatic insertion

Application

- Signal amplification
- Switching circuit

Mechanical data

- **Package:** SOT-363
- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD22-B102CC

■ Maximum Ratings ($T_a=25^{\circ}\text{C}$ Unless otherwise specified)

Item	Symbol	Unit	Conditions	Value
Device marking code				K2X
Collector-base voltage	V_{CBO}	V	$I_C = 100\mu\text{A}, I_E = 0$	60
Collector-emitter voltage	V_{CEO}	V	$I_C = 1\text{mA}, I_B = 0$	40
Emitter-base voltage	V_{EBO}	V	$I_E = 100\mu\text{A}, I_C = 0$	6
Collector current	I_C	mA		600
Power dissipation	P_D	mW		200
Operation junction temperature	T_J	$^{\circ}\text{C}$		-55 to +150
Storage temperature	T_{STG}	$^{\circ}\text{C}$		-55 to +150



MMDT4401

■ Electrical Characteristics (T_a=25°C Unless otherwise specified)

Item	Symbol	Unit	Conditions	Min	Typ	Max
Collector-base breakdown voltage	V _{(BR)CBO}	V	I _C =100μA, I _E =0	60		
Collector-emitter breakdown voltage	V _{(BR)CEO}	V	I _C =1mA, I _B =0	40		
Emitter-base breakdown voltage	V _{(BR)EBO}	V	I _E =100μA, I _C =0	6		
Collector-base cut-off current	I _{CBO}	nA	V _{CE} =50V, I _E =0			100
Collector-emitter cut-off current	I _{CEO}	nA	V _{CE} =35V, I _B =0			500
Emitter-base cut-off current	I _{EBO}	nA	V _{BE} =3V, I _C =0			100
DC current gain	h _{FE1}		V _{CE} =1V, I _C =0.1mA	20		
	h _{FE2}		V _{CE} =1V, I _C =1mA	40		
	h _{FE3}		V _{CE} =1V, I _C =10mA	80		
	h _{FE4}		V _{CE} =1V, I _C =150mA	100		300
	h _{FE5}		V _{CE} =1V, I _C =500mA	40		
Collector-emitter saturation voltage	V _{CE(sat)1}	V	I _C =150mA, I _B =15mA			0.4
	V _{CE(sat)2}		I _C =500mA, I _B =50mA			0.75
Base-emitter saturation voltage	V _{BE(sat)1}	V	I _C =150mA, I _B =15mA			0.95
	V _{BE(sat)2}		I _C =500mA, I _B =50mA			1.2
Transition frequency	f _T	MHz	V _{CE} =10V, I _C =20mA, f=100MHz	250		
Delay time	td	ns	V _{CC} =30V, I _C =150mA, V _{BE} =2V, I _{B1} =15mA			15
Rise time	tr	ns				20
Storage time	ts	ns	V _{CC} =30V, I _C =150mA, I _{B1} =-I _{B2} =5mA			225
Fall time	tf	ns				30

■ Thermal Characteristics

Parameter	Symbol	Unit	Value
Thermal resistance, junction-to-ambient	R _{θJ-A} ⁽¹⁾	°C/W	625
Thermal resistance, junction-to-case	R _{θJ-C} ⁽¹⁾	°C/W	500

Note:

(1) Device mounted on PCB, single-sided copper, with standard footprint



■ Characteristics

Fig 1: Static Characteristics

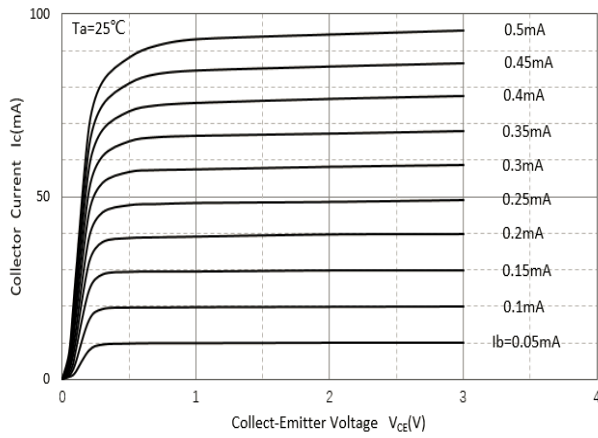


Fig 2: Dc Current Gain

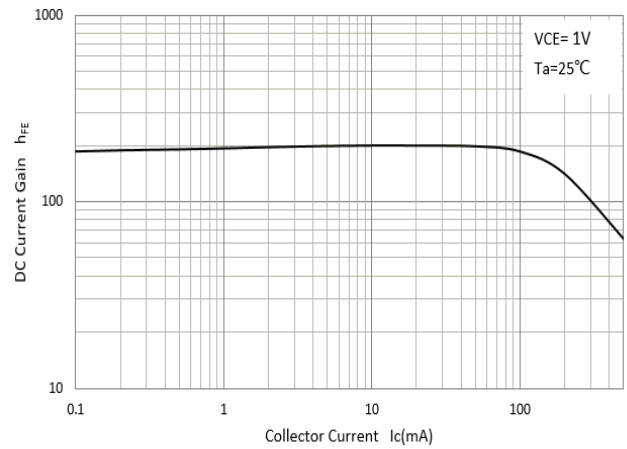


Fig 3: Collector-Emitter Saturation Voltage

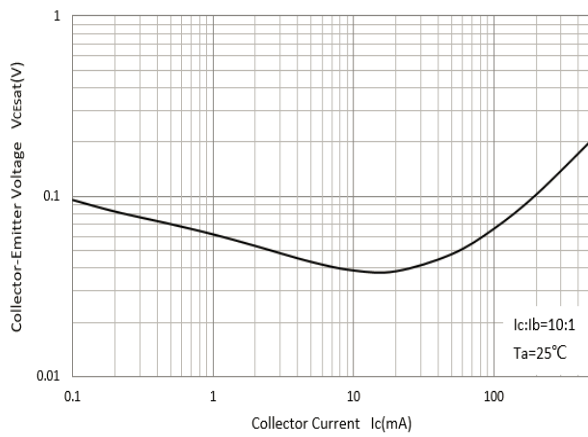


Fig 4: Base-Emitter Saturation Voltage

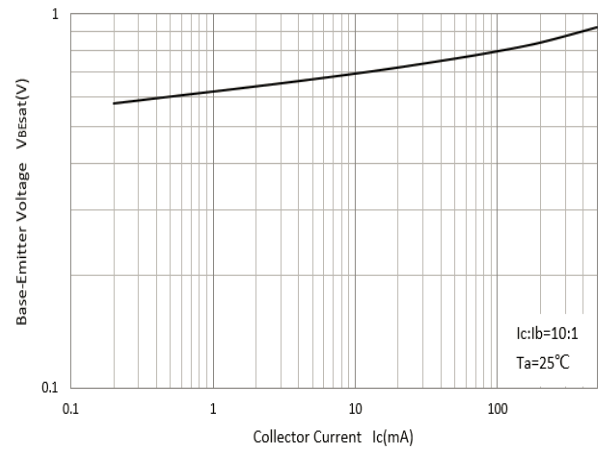


Fig 5: Base-Emitter Voltage

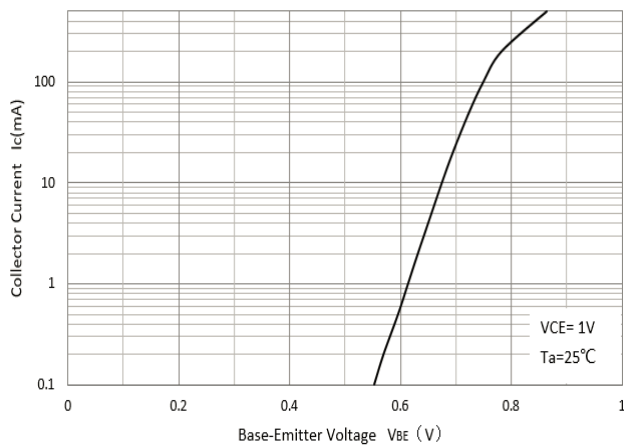


Fig 6: Cob/Cib-V_{CB}/V_{EB}

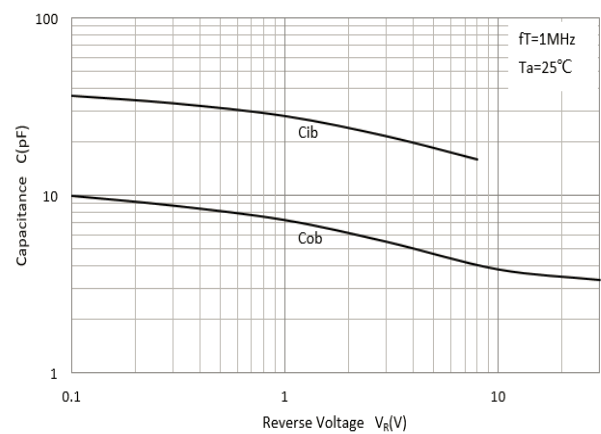
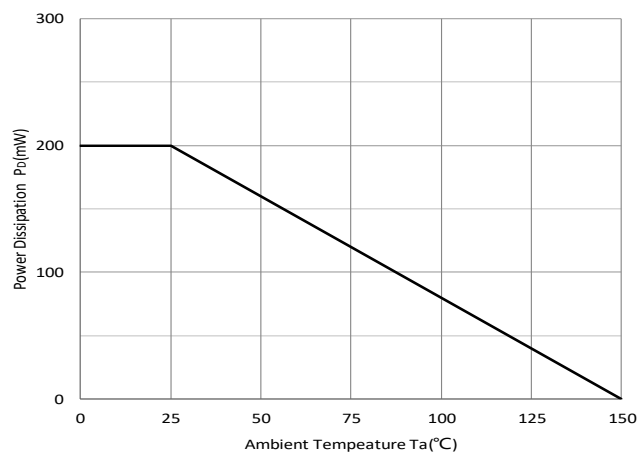




Fig 7: P_D-T_a Curve



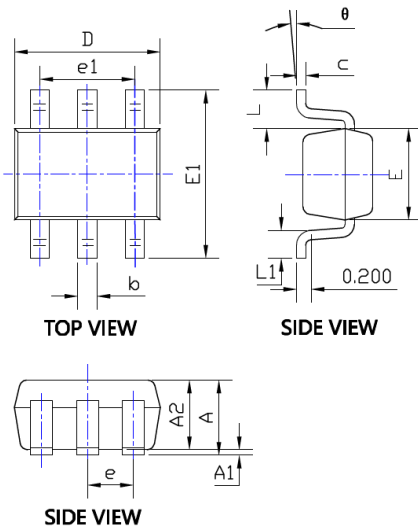
■ Ordering Information

Preferred P/N	Packing code	Unit weight(g)	Minimum package(pcs)	Inner box quantity(pcs)	Outer carton quantity(pcs)	Delivery mode
MMDT4401	F2	Approximate 0.009	3000	30000	120000	7" reel
MMDT4401	F3	Approximate 0.009	10000	/	210000	7" reel



MMDT4401

■ Outline Dimensions

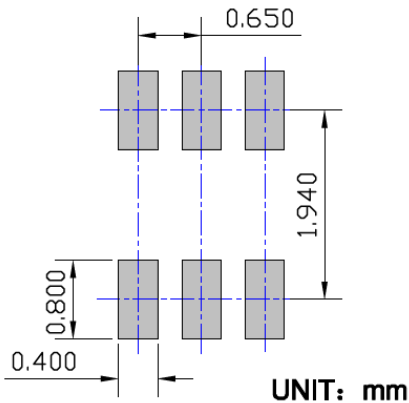


DIMENSIONS				
SYMBOL	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.035	0.043	0.900	1.100
A1	0.000	0.004	0.000	0.100
A2	0.035	0.039	0.900	1.000
b	0.006	0.014	0.150	0.350
c	0.004	0.010	0.100	0.250
D	0.071	0.087	1.800	2.200
E	0.045	0.053	1.150	1.350
E1	0.085	0.096	2.150	2.450
e	0.026TYP		0.650TYP	
e1	0.047	0.055	1.200	1.400
L	0.021REF		0.525REF	
L1	0.010	0.018	0.260	0.460
θ	0°	8°	0°	8°

Note:

1. All dimensions are in millimeters (mm) unless otherwise specified.
[所有尺寸均以毫米为单位, 除非另有说明]
2. General tolerances: $\pm 0.10\text{mm}$ unless otherwise specified.
[通用公差为 $\pm 0.10\text{mm}$, 除非另有说明]
3. Dimensions and tolerances per ASME Y14.5M-2018.
[尺寸和公差遵循 ASME Y14.5M-2018 标准]
4. All dimensions shown are exclusive of burrs and gate residues.
Burrs and gate vestiges shall not exceed 0.15 mm in maximum.
[所有尺寸均不包括毛刺和浇口残留。毛刺与浇口残留的尺寸最大不得超过 0.15mm]
5. Dimension b does not include dambar protrusion of max 0.100 mm per side.
[尺寸b不包括单边最大0.100 MM的中筋凸出部分]
6. Dimensions D and E are the overall extreme outer dimensions of the mold compound. These dimensions exclude mold flash, lead flash, protrusions and burrs but include the maximum allowable mold mismatch.
[D和E是塑封体的外部极限尺寸, 不包括包封溢料、内引线溢料、凸出部分以及胶体毛刺, 但是包含了包封错位的最大尺寸]
7. Formed leads shall be planar with respect to one another within a maximum of 0.076 mm relative to the seating plane.
[成型的管脚应为同一平面, 共面性最大为0.1mm]

■ Suggested Pad Layout





MMDT4401

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